

RoHS Compliant

PCI Express Flash Drive

PT120-M280 Product Specifications



August 4, 2020 Version 1.1



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Specifications Overview:

- PCle Interface
 - Compliant with NVMe 1.2
 - Compatible with PCIe Gen3 x2 interface
- Capacity
 - Single side: 120, 240 GB
 - Double side: 480 GB
- Performance*
 - Interface burst read/write: 2 GB/sec
 - Sequential read: up to 1,600 MB/sec
 - Sequential write: up to 1,035 MB/sec
 - Random read (4K): up to 170,000 IOPS
 - Random write (4K): up to 190,000 IOPS
- Flash Management
 - Low-Density Parity-Check (LDPC) Code
 - Global Wear Leveling
 - Flash bad-block management
 - Flash Translation Layer: Page Mapping
 - S.M.A.R.T.
 - Power Failure Management
 - TRIM
 - Hyper Cache Technology
 - Over-Provisioning
 - DataRAID[™]
- Security
 - AES 256-bit hardware encryption
 - End-to-End Data Protection
- NAND Flash Type: 3D TLC (BiCS3)
- MTBF: >3,000,000 hours
- Endurance (in drive writes per day : DWPD)
 - 120 GB: 1.32 DWPD
 - 240 GB: 1.14 DWPD
 - 480 GB: 1.01 DWPD

- Temperature Range
 - Operating: 0°C to 70°C
 - Storage: -40°C to 100°C
- Supply Voltage
 - 3.3 V ± 5%
- Power Consumption*
 - Active mode: 1,010 mA
 - Idle mode: 155 mA
- Connector Type
 - 75-pin M.2 module pinout
- Power Management
 - Supports APST
 - Supports ASPM L1.2
- DRAM Cache for Enhanced Random Performance
- Reliability
 - Thermal Sensor
 - Thermal Throttling
- Form Factor
 - M.2 2280-S3-B-M: 120, 240 GB
 - M.2 2280-D5-B-M: 480 GB
 - Dimensions:
 Single side: 80.00 x 22.00 x 2.38, unit: mm
 Double side: 80.00 x 22.00 x 3.88, unit: mm

1

- Net Weight: 6.80 g
- LED Indicators for Drive Behavior
- RoHS Compliant

*Varies from capacities. The values for performances and power consumptions presented are typical and may vary depending on flash configurations or platform settings.

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1. General Descriptions

Apacer PT120-M280 (M.2 2280) is the next generation modularized Solid State Drive (SSD) with the shape of all new M.2 form factor, aimed to be the more suitable for mobile and compact computers with standard width at only 22.00 mm. PT120-M280 appears in M.2 2280 mechanical dimensions and is believed to be the leading add-in storage solution for future host computing systems.

The M.2 SSD is designed with PCIe-based connector pinouts, providing full compliance with the latest PCIe Gen3 x2 interface specifications. Aside from PCIe compliance, PT120-M280 delivers exceptional performance and power efficiency. On the other hand, the extreme thin and light form factor makes PT120-M280 the ideal choice for mobile computing systems, which appears to be the trend in near future.

Regarding reliability, PT120-M280 is built with a powerful PCIe controller that supports on-the-module ECC as well as efficient wear leveling scheme. In terms of power efficiency, PT120-M280 is compliant with PCIe Gen3 x2 interface standard so that it can operate on power management modes, which greatly save on power consumption.

2. Functional Block

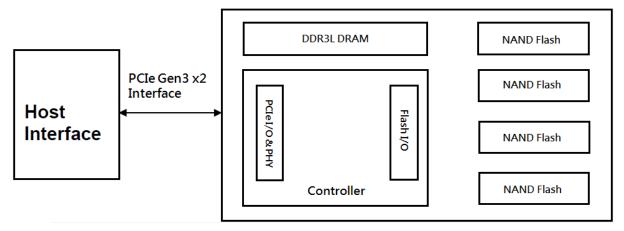


Figure 2-1 Functional Block Diagram

3. Pin Assignments

This connector does not support hot plug capability. There are a total of 75 pins. 12 pin locations are used for mechanical key locations; this allows such a module to plug into both Key B and Key M connectors.

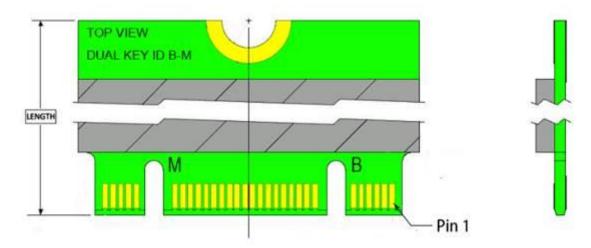


Table 3	-1 Pin	Assignments
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Pin	Туре	Description
1	GND	CONFIG_3 = GND
2	3.3V	3.3V source
3	GND	Ground
4	3.3V	3.3V source
5	N/C	No connect
6	N/C	No connect
7	N/C	No connect
8	N/C	No connect
9	N/C	No connect
10	DAS/DSS	Device Activity Signal/Disable Staggered Spin-up
11	N/C	No connect
12	(removed for key)	Mechanical notch B
13	(removed for key)	Mechanical notch B
14	(removed for key)	Mechanical notch B
15	(removed for key)	Mechanical notch B
16	(removed for key)	Mechanical notch B
17	(removed for key)	Mechanical notch B
18	(removed for key)	Mechanical notch B
19	(removed for key)	Mechanical notch B
20	N/C	No connect
21	GND	CONFIG_0=GND
22	N/C	No connect
23	N/C	No connect
24	N/C	No connect
25	N/C	No connect
26	N/C	No connect
27	GND	Ground
28	N/C	No connect
29	PETn1	PCIe TX Differential signal defined by the PCI Express M.2 spec
30	N/C	No connect
31	PETp1	PCIe TX Differential signal defined by the PCI Express M.2 spec

Pin	Туре	Description
32	N/C	No connect
33	GND	Ground
34	N/C	No connect
35	PERn1	PCIe RX Differential signal defined by the PCI Express M.2 spec
36	N/C	No connect
37	PERp1	PCIe RX Differential signal defined by the PCI Express M.2 spec
38	N/C GND	No connect
39		Ground
40	SMB_CLK (I/O)(0/1.8V)	SMBus Clock; Open Drain with pull-up on platform
41	PETn0	PCIe TX Differential signal defined by the PCI Express M.2 spec
42	SMB_DATA (I/O)(0/1.8V)	SMBus Data; Open Drain with pull-up on platform.
43	PETp0	PCIe TX Differential signal defined by the PCI Express M.2 spec
44	ALERT#(O) (0/1.8V)	Alert notification to master; Open Drain with pull-up on platform; Active low.
45	GND	Ground
46	N/C	No connect
47	PERn0	PCIe RX Differential signal defined by the PCI Express M.2 spec
48	N/C	No connect
49	PERp0	PCIe RX Differential signal defined by the PCI Express M.2 spec
		PE-Reset is a functional reset to the card as
50	PERST#(I)(0/3.3V)	defined by the PCIe Mini CEM specification.
51	GND	Ground
52	CLKREQ#(I/O)(0/3.3V)	Clock Request is a reference clock request signal as defined by the PCIe Mini CEM specification; Also used by L1 PM Sub-states.
53	REFCLKn	PCIe Reference Clock signals (100 MHz) defined by the PCI Express M.2 spec.
54	PEWAKE#(I/O)(0/3.3V)	PCIe PME Wake. Open Drain with pull up on platform; Active Low.
55	REFCLKp	PCIe Reference Clock signals (100 MHz) defined by the PCI Express M.2 spec.
	Deserved for	Manufacturing Data line. Used for SSD manufacturing only.
	Reserved for	Not used in normal operation.
56	MFG DATA	Pins should be left N/C in platform Socket.
57	GND	Ground
58	Reserved for MFG CLOCK	Manufacturing Clock line. Used for SSD manufacturing only. Not used in normal operation. Pins should be left N/C in platform Socket.
59	(removed for key)	Mechanical notch M
60	(removed for key)	Mechanical notch M
61	(removed for key)	Mechanical notch M
62	(removed for key)	Mechanical notch M
63	(removed for key)	Mechanical notch M
64	(removed for key)	Mechanical notch M
	(removed for key)	
65 66	(removed for key)	Mechanical notch M Mechanical notch M
67	NC	No connect (used for other purposes)
07		
60	SUSCLK(32KHz)	32.768 kHz clock supply input that is provided by the platform chipset to
68	(I)(0/3.3V)	reduce power and cost for the module.
69	NC 2 2V	CONFIG_1 = No connect
70	3.3V	Supply pin, 3.3V
71	GND	Ground
72	3.3V	Supply pin, 3.3V
73	GND	Ground
74	3.3V	Supply pin, 3.3V
75	CONFIG_2	Ground

4. Product Specifications

4.1 Capacity

Capacity specifications of PT120-M280 are available as shown in Table 4-1. It lists the specific capacity and the default numbers of heads, sectors and cylinders for each product line.

Capacity	Total bytes*	Cylinders	Heads	Sectors	Total LBA
120 GB	120,034,123,776	16,383	16	63	234,441,648
240 GB	240,057,409,536	16,383	16	63	468,862,128
480 GB	480,103,981,056	16,383	16	63	937,703,088

Table 4-1 Capacity Specifications

*Display of total bytes varies from file systems, which means not all of the bytes can be used for storage.

**Notes: 1 GB = 1,000,000,000 bytes; 1 sector = 512 bytes.

LBA count addressed in the table above indicates total user storage capacity and will remain the same throughout the lifespan of the device. However, the total usable capacity of the SSD is most likely to be less than the total physical capacity because a small portion of the capacity is reserved for device maintenance usages.

4.2 Performance

Performance of PT120-M280 is listed below in Table 4-2.

Table 4-2 Performance Specifications

Capacity Performance	120 GB	240 GB	480 GB
Sequential Read* (MB/s)	1,515	1,580	1,600
Sequential Write* (MB/s)	460	855	1,035
Random Read IOPS** (4K)	84,000	138,000	170,000
Random Write IOPS** (4K)	102,000	169,000	190,000

Note:

Results may differ from various flash configurations or host system setting.

*Sequential performance is based on CrystalDiskMark 5.2.1 with file size 1,000MB.

**Random performance measured using IOMeter with Queue Depth 32.

4.3 Environmental Specifications

Environmental specifications of PT120-M280 are shown in Table 4-3.

Table 4-3 Environmental Specifications

Specifications
0°C to 70°C
-40°C to 100°C
7.69 GRMS, 20~2000 Hz/random (compliant with MIL-STD-810G)
4.02 GRMS, 15~2000 Hz/random (compliant with MIL-STD-810G)
50(G), 11(ms), half-sine wave
1,500(G), 0.5(ms), half-sine wave

Note: Shock and Vibration specifications are subject to change without notice.

4.4 Mean Time Between Failures (MTBF)

Mean Time Between Failures (MTBF) is predicted based on reliability data for the individual components in PT120-M280. The prediction result for PT120-M280 is more than 3,000,000 hours.

Note: The MTBF is predicated and calculated based on "Telcordia Technologies Special Report, SR-332, Issue 3" method.

4.5 Certification and Compliance

PT120-M280 complies with the following standards:

- FCC
- CE
- RoHS
- MIL-STD-810

4.6 Endurance

The endurance of a storage device is predicted by Drive Writes Per Day based on several factors related to usage, such as the amount of data written into the drive, block management conditions, and daily workload for the drive. Thus, key factors, such as Write Amplifications and the number of P/E cycles, can influence the lifespan of the drive.

Capacity	Drive Writes Per Day
120 GB	1.32
240 GB	1.14
480 GB	1.01

Table 4-4 Drive Writes Per Day

Note:

- This estimation complies with JEDEC JESD-219A random client workload.
- Flash vendor guaranteed 3D NAND TLC P/E cycle: 3K
- WAF may vary from capacity, flash configurations and writing behavior on each platform.
- 1 Terabyte = 1,024GB
- DWPD (Drive Writes Per Day) is calculated based on the number of times that user overwrites the entire capacity of an SSD per day of its lifetime during the warranty period. (3D NAND TLC warranty: 2 years)

4.7 LED Indicator Behavior

The behavior of the PT120-M280 LED indicators is described in Table 4-5.

Table 4-5 LED Behavior

Location	LED	Description
LED A	DAS	LED blinks when the drive is being accessed



5. Flash Management

5.1 Error Correction/Detection

PT120-M280 implements a hardware ECC scheme, based on the Low Density Parity Check (LDPC). LDPC is a class of linear block error correcting code which has apparent coding gain over BCH code because LDPC code includes both hard decoding and soft decoding algorithms. With the error rate decreasing, LDPC can extend SSD endurance and increase data reliability while reading raw data inside a flash chip.

5.2 Bad Block Management

Current production technology is unable to guarantee total reliability of NAND flash memory array. When a flash memory device leaves factory, it comes with a minimal number of initial bad blocks during production or out-of-factory as there is no currently known technology that produce flash chips free of bad blocks. In addition, bad blocks may develop during program/erase cycles. Since bad blocks are inevitable, the solution is to keep them in control. Apacer flash devices are programmed with ECC, page mapping technique and S.M.A.R.T to reduce invalidity or error. Once bad blocks are detected, data in those blocks will be transferred to free blocks and error will be corrected by designated algorithms.

5.3 Global Wear Leveling

Flash memory devices differ from Hard Disk Drives (HDDs) in terms of how blocks are utilized. For HDDs, when a change is made to stored data, like erase or update, the controller mechanism on HDDs will perform overwrites on blocks. Unlike HDDs, flash blocks cannot be overwritten and each P/E cycle wears down the lifespan of blocks gradually. Repeatedly program/erase cycles performed on the same memory cells will eventually cause some blocks to age faster than others. This would bring flash storages to their end of service term sooner. Global wear leveling is an important mechanism that levels out the wearing of all blocks so that the wearing-down of all blocks can be almost evenly distributed. This will increase the lifespan of SSDs.

5.4 Flash Translation Layer – Page Mapping

Page mapping is an advanced flash management technology whose essence lies in the ability to gather data, distribute the data into flash pages automatically, and then schedule the data to be evenly written. Page-level mapping uses one page as the unit of mapping. The most important characteristic is that each logical page can be mapped to any physical page on the flash memory device. This mapping algorithm allows different sizes of data to be written to a block as if the data is written to a data pool and it does not need to take extra operations to process a write command. Thus, page mapping is adopted to increase random access speed and improve SSD lifespan, reduce block erase frequency, and achieve optimized performance and lifespan.

5.5 Power Failure Management

Power Failure Management plays a crucial role when experiencing unstable power supply. Power disruption may occur when users are storing data into the SSD. In this urgent situation, the controller would run multiple flush cycles to store the metadata for later block rebuilding. This urgent operation requires about several milliseconds to get it done. At the next power up, the firmware will perform a status tracking to retrieve the mapping table and resume previously programmed NAND blocks to check if there is any incompleteness of transmission.

Note: The controller unit of this product model is designed with a DRAM as a write cache for improved performance and data efficiency. Though unlikely to happen in most cases, the data cached in the volatile DRAM might be potentially affected if a sudden power loss takes place before the cached data is flushed into non-volatile NAND flash memory.

5.6 TRIM

TRIM is a feature which helps improve the read/write performance and speed of solid-state drives (SSD). Unlike hard disk drives (HDD), SSDs are not able to overwrite existing data, so the available space gradually becomes smaller with each use. With the TRIM command, the operating system can inform the SSD which blocks of data are no longer in use and can be removed permanently. Thus, the SSD will perform the erase action, which prevents unused data from occupying blocks all the time.

5.7 Hyper Cache Technology

Apacer proprietary Hyper Cache technology uses a portion of the available capacity as SLC (1bit-percell) NAND flash memory, called Hyper cache mode. When data is written to SSD, the firmware will direct the data to Hyper Cache mode, providing excellent performance to handle various scenarios in industrial use.

5.8 Over-Provisioning

Over-Provisioning (OP) is a certain portion of the SSD capacity exclusively for increasing Garbage Collection (GC) efficiency, especially when the SSD is filled to full capacity or performs a heavy mixed-random workload. OP has the advantages of providing extended life expectancy, reliable data integrity, and high sustained write performance.

5.9 DataRAID[™]

Apacer's DataRAID algorithm applies an additional level of protection and error-checking. Using this algorithm, a certain amount of space is given over to aggregating and resaving the existing parity data used for error checking. So, in the event that data becomes corrupted, the parity data can be compared to the existing uncorrupted data and the content of the corrupted data can be rebuilt.

6. Security & Reliability Features

6.1 Advanced Encryption Standard

Advanced Encryption Standard (AES) is a specification for the encryption of electronic data. AES has been adopted by the U.S. government since 2001 to protect classified information and is now widely implemented in embedded computing applications. The AES algorithm used in software and hardware is symmetric so that encrypting/decrypting requires the same encryption key. Without the key, the encrypted data is inaccessible to ensure information security.

Notably in flash memory applications, AES 256-bit hardware encryption is the mainstream to protect sensitive or confidential data. The hardware encryption provides better performance, reliability, and security than software encryption. It uses a dedicated processor, which is built inside the controller, to process the encryption and decryption. This enormously shortens the processing time and makes it efficient.

6.2 End-to-End Data Protection

End-to-End Data Protection is a feature implemented in Apacer SSD products that extends error control to cover the entire path from the host computer to the drive and back, and that ensures data integrity at multiple points in the path to enable reliable delivery of data transfers. Unlike ECC which does not exhibit the ability to determine the occurrence of errors throughout the process of data transmission, End-to-End Data Protection allows SSD controller to identify an error created anywhere in the path and report the error to the host computer before it is written to the drive. This error-checking and error-reporting mechanism therefore guarantees the trustworthiness and reliability of the SSD.

6.3 Thermal Sensor

Apacer Thermal Sensor is a digital temperature sensor with serial interface. By using designated pins for transmission, storage device owners are able to read temperature data.

6.4 Thermal Throttling

Thermal throttling can monitor the temperature of the SSD equipped with a built-in thermal sensor via S.M.A.R.T. commands. This method can ensure the temperature of the device stays within temperature limits by drive throttling, i.e. reducing the speed of the drive when the device temperature reaches the threshold level, so as to prevent overheating, guarantee data reliability, and prolong product lifespan. When the temperature exceeds the maximum threshold level, thermal throttling will be triggered to reduce performance step by step to prevent hardware components from being damaged. Performance is only permitted to drop to the extent necessary for recovering a stable temperature to cool down the device's temperature. Once the temperature decreases to the minimum threshold value, transfer speeds will rise back to its optimum performance level.

7. Software Interface

7.1 Command Set

Table 7-1 summarizes the commands supported by PT120-M280.

Opcode	Command Description
00h	Delete I/O Submission Queue
01h	Create I/O Submission Queue
02h	Get Log Page
04h	Delete I/O Completion Queue
05h	Create I/O Completion Queue
06h	Identify
08h	Abort
09h	Set Features
0Ah	Get Features
0Ch	Asynchronous Event Request
10h	Firmware Activate
11h	Firmware Image Download

Table 7-1 Admin Commands

Table 7-2 Admin Commands - NVM Command Set Specific

Opcode	Command Description					
80h	Format NVM					
81h	Security Send					
82h	Security Receive					

Table 7-3 NVM Commands

Opcode	Command Description
00h	Flush
01h	Write
02h	Read
04h	Write Uncorrectable
05h	Compare
08h	Write Zeroes
09h	Dataset Management

7.2 S.M.A.R.T.

SMART, an acronym for Self-Monitoring, Analysis and Reporting Technology, is an open standard that allows a hard disk drive to automatically detect its health and report potential failures. When a failure is recorded by SMART, users can choose to replace the drive to prevent unexpected outage or data loss. Moreover, SMART can inform users of impending failures while there is still time to perform proactive actions, such as copy data to another device.

Byte	Length	Description			
0	1	Critical Warning			
1-2	2	Composite Temperature			
3	1	Available Spare			
4	1	Available Spare Threshold			
5	1	Percentage Used			
6-31	26	Reserved			
32-47	16	Data Units Read			
48-63	16	Data Units Written			
64-79	16	Host Read Commands			
80-95	16	Host Write Commands			
96-111	16	Controller Busy Time			
112-127	16	Power Cycles			
128-143	16	Power On Hours			
144-159	16	Unsafe Shutdowns			
160-175	16	Media and Data Integrity Errors			
176-191	16	Number of Error Information Log Entries			
192-195	4	Warning Composite Temperature Time			
196-199	4	Critical Composite Temperature Time			
200-201	2	Temperature Sensor 1			
202-203	2	Temperature Sensor 2			
204-205	2	Temperature Sensor 3			
206-207	2	Temperature Sensor 4			
208-209	2	Temperature Sensor 5			
210-211	2	Temperature Sensor 6			
212-213	2	Temperature Sensor 7			
214-215	2	Temperature Sensor 8			
216-511	296	Reserved			

Table 7-4 SMART (02h)

Table 7-5 SMART (C0h)

Byte	Length	Description
2-255	254	Reserved
256-257	2	SSD Protect Mode
258-261	4	ECC Fail Count
262-273	12	Reserved
274-277	4	Total Later Bad Block Count
278-281	4	Max Erase Count
282-285	4	Average Erase Count
286-289	4	Program Fail Count
290-293	4	Erase Fail Count
294-301	8	FlashWriteSector
302-511	210	Reserved

8. Electrical Specifications

8.1 Operating Voltage

Table 8-1 lists the supply voltage for PT120-M280.

Table 8-1 Operating Range

Item	Range
Supply Voltage	3.3V ± 5%

8.2 Power Consumption

Table 8-2 lists the power consumption for PT120-M280.

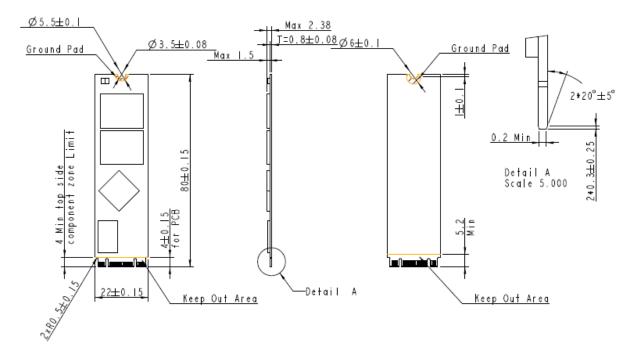
Table 8-2 Power Consumption

Capacity Mode	120 GB	240 GB	480 GB
Active (mA)	845	935	1,010
Idle (mA)	150	150	155
Note:		•	•

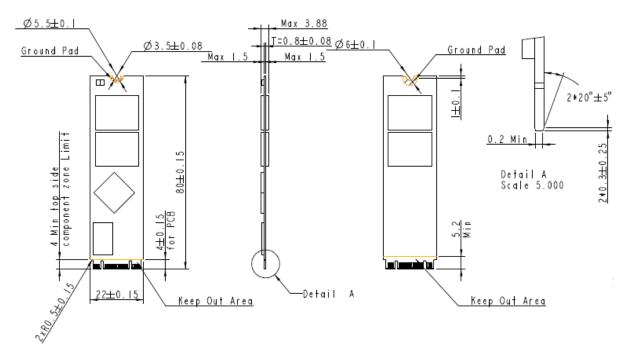
Note: *All values are typical and may vary depending on flash configurations or host system settings. **Active power is an average power measurement performed using CrystalDiskMark with 128KB sequential read/write transfers.

9. Physical Characteristics

9.1 Single Side



9.2 Double Side



9.3 Net Weight

Capacity	Net Weight (g)
120GB	5.75
240GB	5.75
480GB	6.80

10. Product Ordering Information

10.1 Product Code Designations

Codo	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
Code	В	9	2		1	2	5	Х	G	Х		Х	Х	Х	0	3

Code 1-3 (Product Line & form factor)	PCIe M280
Code 5-6 (Model/Solution)	PT120-M280
Code 7-8 (Product Capacity)	5H: 120GB 5J: 240GB 5K: 480GB
Code 9 (Flash Type & Product Temp)	G: 3D TLC Standard temperature
Code 10 (Product Spec)	A: Single side B+M key B: Double side B+M key
Code 12-14 (Version Number)	Random numbers generated by system
Code 15-16 (Firmware Version)	03: Standard

10.2 Valid Combinations

Capacity	Part Number
120GB	B92.125HGA.00103
240GB	B92.125JGA.00103
480GB	B92.125KGB.00103

Note: Valid combinations are those products in mass production or will be in mass production. Consult your Apacer sales representative to confirm availability of valid combinations and to determine availability of new combinations.

Revision History

Revision	Description	Date
0.1	Preliminary release	5/2/2019
1.0	Updated the length and description of bytes 2-255 and 262-273 for Table 7-5 SMART (C0h) at 7.2 S.M.A.R.T.	6/26/2019
1.1	- Updated MTBF on Specifications Overview page and 4.4 Mean Time Between Failures (MTBF) by changing it from >1,000,000 hours to >3,000,000 hours and issue method from 2 to 3	
	- Updated Table 4-1 by changing max LBA to total LBA	8/4/2020
	 Added a note regarding DRAM cache to 5.5 Power Failure Management 	

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